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(54) **BONDING STRUCTURE AND METHOD FOR PRODUCING BONDING STRUCTURE**

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(57) **ABSTRACT**

A bonding structure (100) of the present invention includes a substrate (110), a metal film (120), a semiconductor element (130). The substrate (110), the metal film (120), and the semiconductor element (130) are laminated in order just mentioned. The metal film (120) contains a metal diffused through stress migration, and the substrate (110) and the semiconductor element (130) are bonded together with the metal film (120) therebetween.

